



# **ECE695: Reliability Physics of Nano-Transistors**

## **Lecture 40: Failure Analysis and Epilogue**

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# Outline

1. Plan experiments, test carefully, and then post-mortem
2. Summary: NBTI, HCI, TDDB, Radiation
3. Summary: Measurement and Data Analysis
4. Summary: Why I work on this field
5. Conclusion

# CSI: Failure case studies

1. Field returns of Agere hard disk – the issue of cheap fan.
2. Field returns of IBM Chip – Po contamination during cleaning of bottles
3. Story of liberty ships during second world war – Welding vs. bolting.
4. Comet explosion in Calcutta on May 02, 1953.  
( <http://aviation-safety.net/database/record.php?id=19530502-0> )

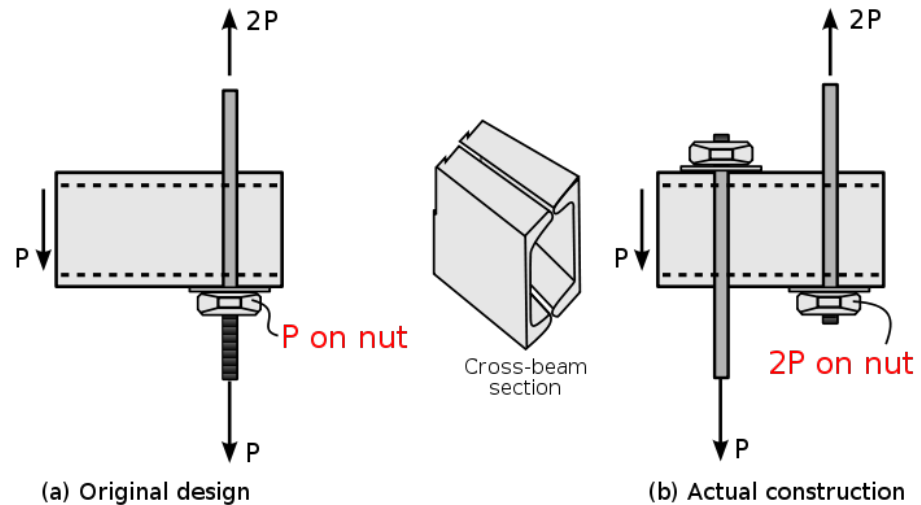
Reliability is a system issue; cascading effects of isolated events

# Failure case studies

## 1. Hyatt Regency walkway collapse , Oct. 14, 1978.



Wikipedia



Three days after the disaster, Wayne Lischka, a [structural engineer](#) hired by [The Kansas City Star newspaper](#), discovered a significant change in the design of the walkways. Coverage of the event later earned the *Star* and its sister publication the [Kansas City Times](#) a [Pulitzer Prize](#) for local news reporting in 1982.

# Instrumentation needed: Microscopes

## Microscopes (e.g.

[Optical microscope](#) ,

[Scanning acoustic microscope](#) (SAM)

Scanning Acoustic Tomography (SCAT),

[Atomic Force Microscope](#) (AFM)

[X-ray microscope](#), [Scanning SQUID microscope](#)

## Scanning Electron Microscopy

[Scanning electron microscope](#) (SEM)

[Electron beam induced current](#) (EBIC) in SEM

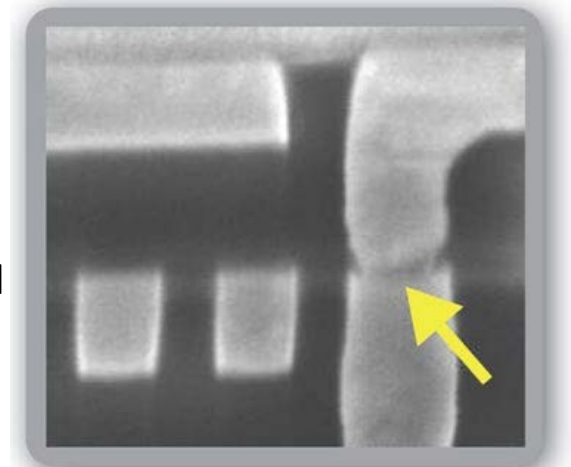
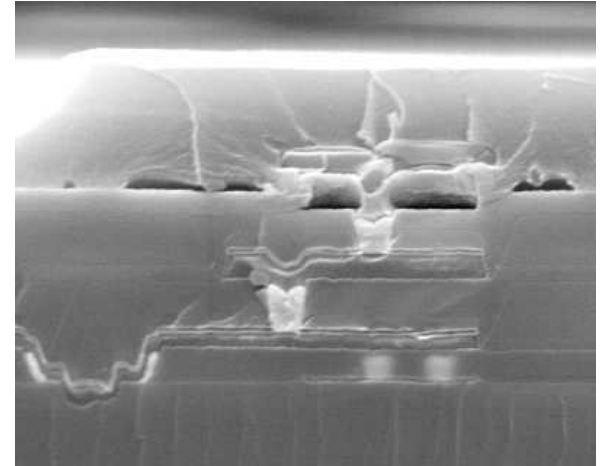
[Charge Induced Voltage Alteration](#) (CIVA) in SEM

[Voltage contrast](#) in SEM

[Electron backscatter diffraction](#) (EBSD) in SEM

[Energy Dispersive X-ray Spectroscopy](#) (EDS) in SEM

[Transmission electron microscope](#) (TEM)



# Instrumentation needed

## Sample Preparation

[Jet-etcher](#), [Plasma etcher](#), [Back Side Thinning Tools](#) , [Focused ion beam](#) etching (FIB)

## Spectroscopic Analysis

[Transmission line](#) pulse spectroscopy (TLPS), [Auger electron spectroscopy](#)  
[Deep Level Transient Spectroscopy](#) (DLTS)

## Laser Signal Injection Microscopy (LSIM)

Photo carrier stimulation

Static

[Optical beam induced current](#) (OBIC)

[Light Induced Voltage Alteration](#) (LIVA)

Dynamic

[Laser Assisted Device Alteration](#) (LADA)

## Software Based Fault Location Techniques

[CAD Navigation](#)

[Automatic Test Pattern Generation](#) (ATPG)

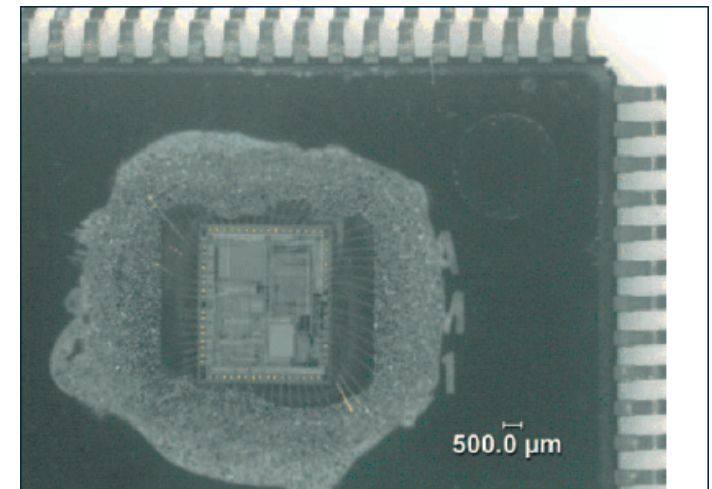
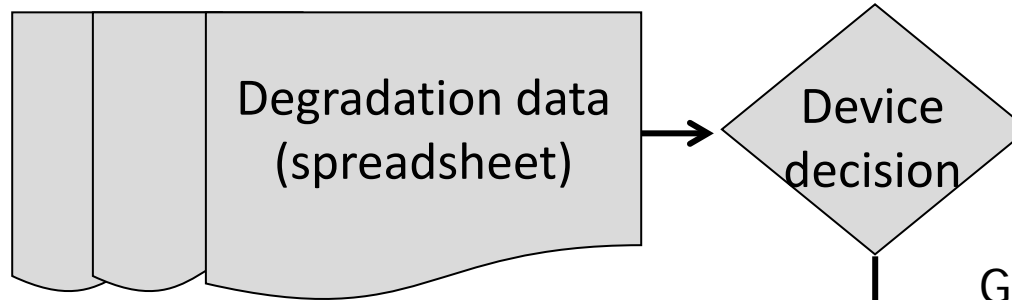


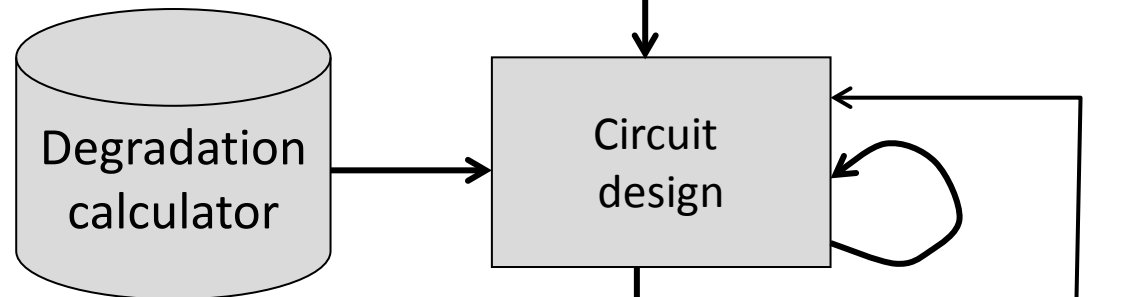
Figure 4-3: De-capped IC.

# CAD Tool: An Example from Texas Instruments

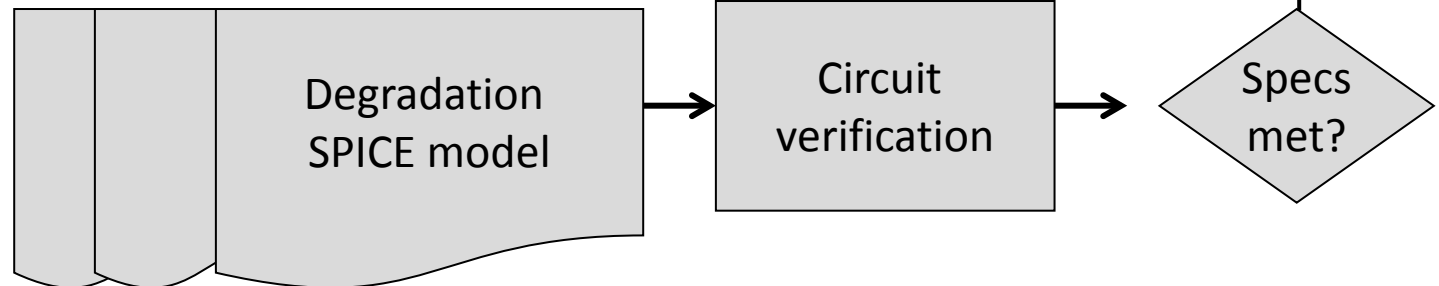
## Component Decision Phase



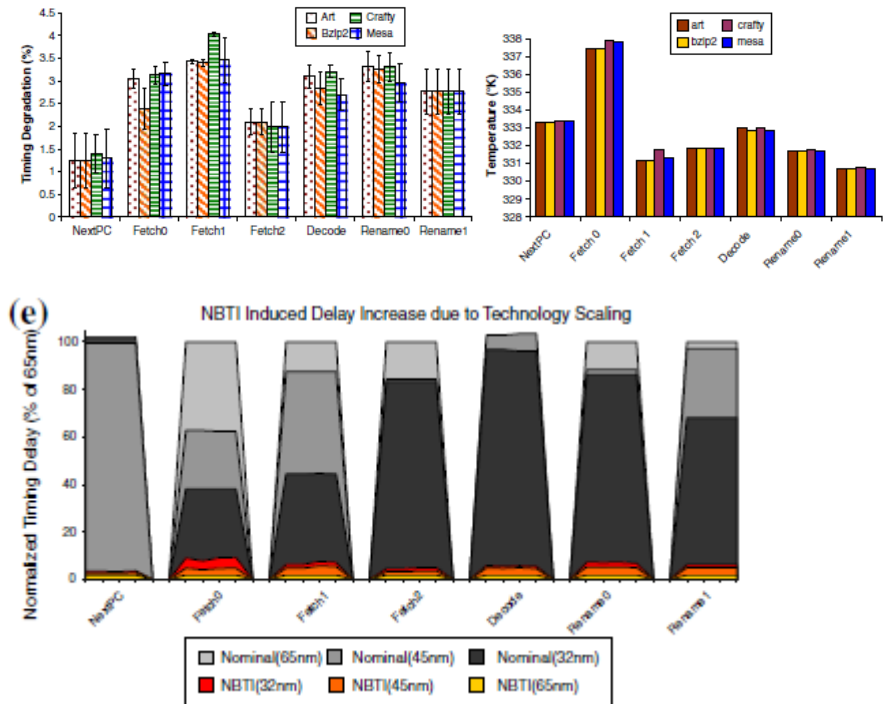
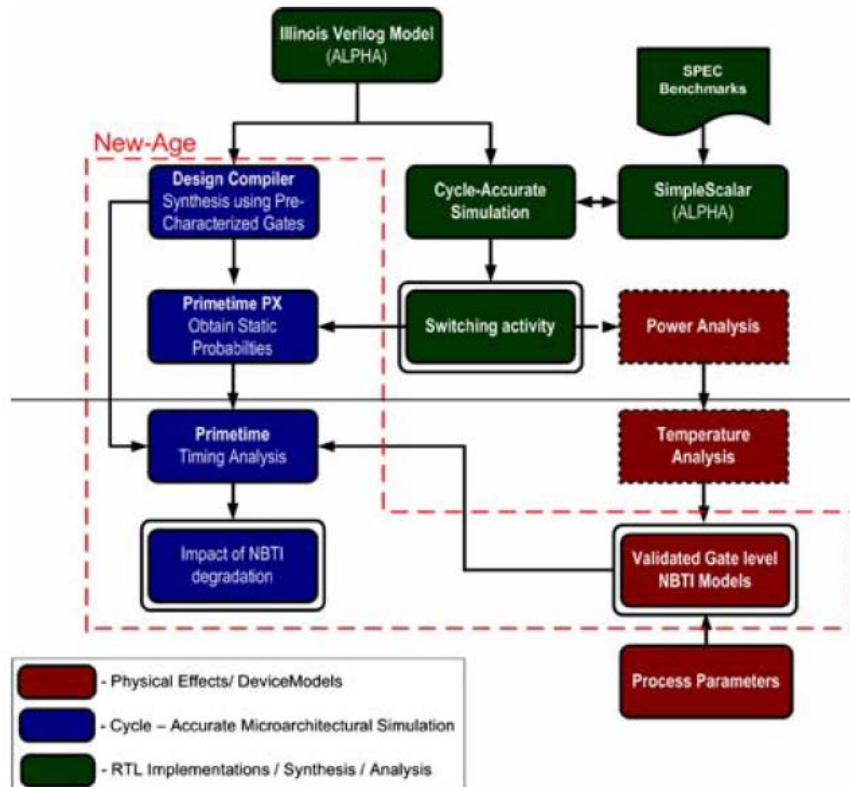
## Circuit Design Phase



## Circuit Verification Phase



# CAD Tool: New-Age from Arizona State



M. DeBole, Int. J. Parallel Prog. 2009.

Stagenet from GSRC manages Floorplanning for smooth stressing.



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- 2. Summary: NBTI, HCI, TDDB, Radiation**
3. Summary: Measurement and Data Analysis
4. Summary: Solutions by Statistical design by Circuits and Systems
5. Conclusion

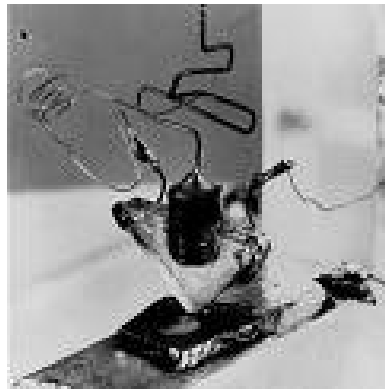
# Technology & transistors in electronics

Vacuum  
Tubes



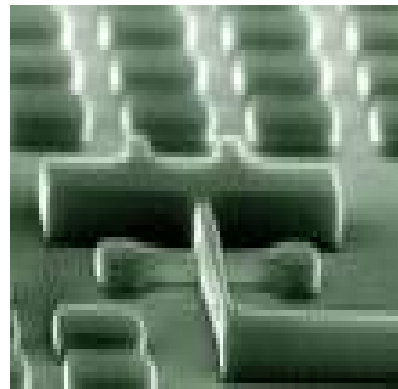
1906-1950s

Bipolar

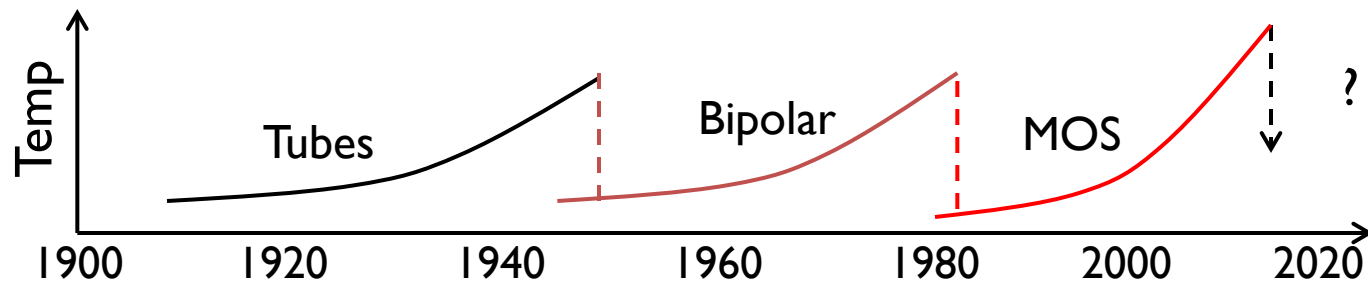


1947-1980s

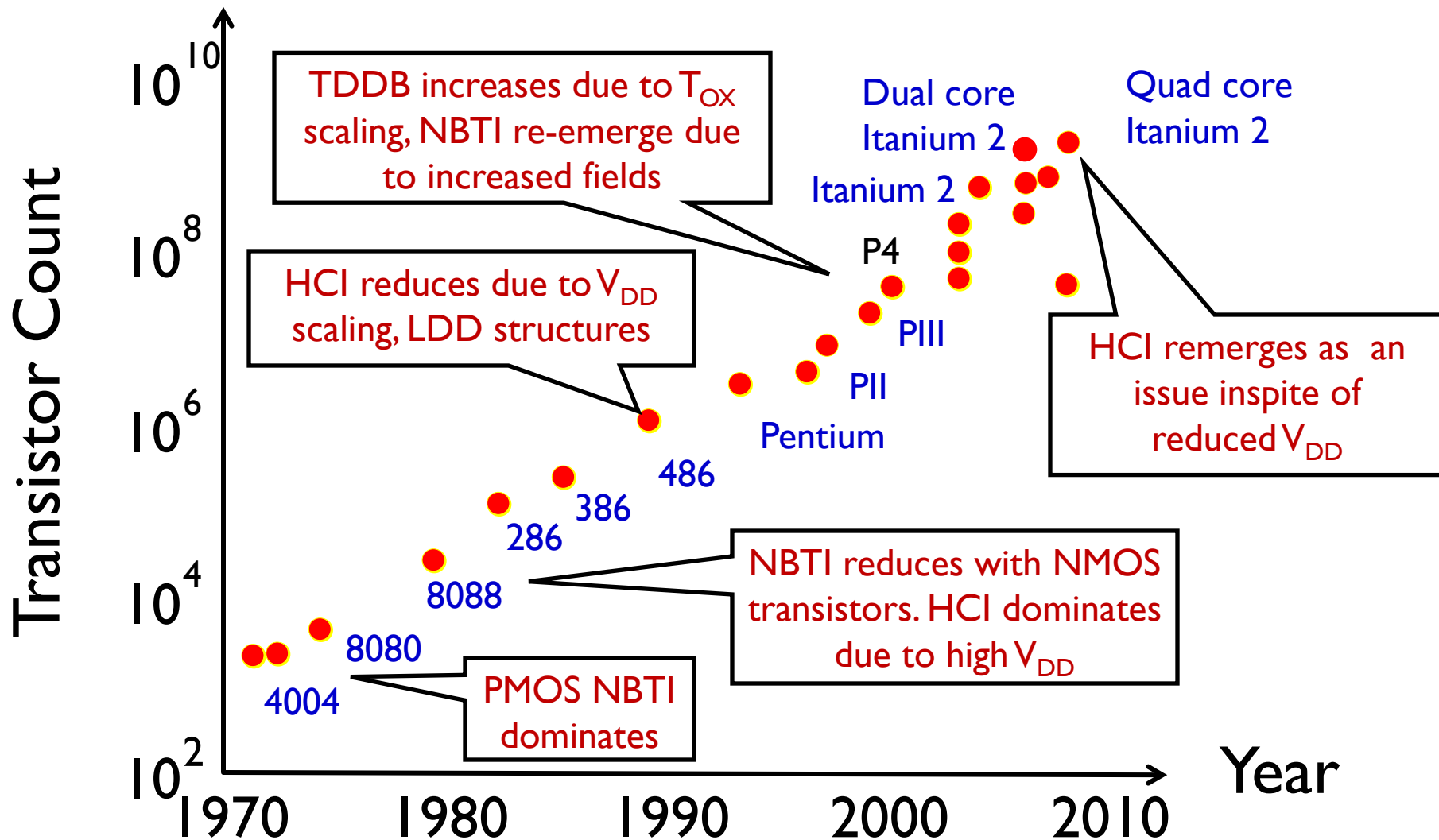
MOSFET



1960-until now



# Scaling and reliability: A short history



# Defects and Coordination

1. Crystalline, poly-crystalline, and a-materials all have a broad range of applications in IC industry. They appear very different initially.
2. We learned that a-material is not really random and it is easy to calculate the size-distribution from elementary theory.
3. Recall Euler and Maxwell relationships in understanding coordination and defect formation. An amorphous material need not be defective. A-Si has fewer types of defects, but more of them.

# NBTI degradation

1. PMOS specific degradation
2. Degradation described by power-laws arising from Reaction-Diffusion model. Frequency independent; S-shaped duty cycle dependence
3. Complex field acceleration based on polarization
4. Non-Arrhenius temperature activation
5. Circuits techniques are often needed to address NBTI problems.

# HCI degradation

1. Both NMOS/PMOS may be affected. Still a concern even with voltages close to 1V
2. Time-Universality is a key feature.
3. Hot carrier driven voltage acceleration; can be obtained from scaling theory.
4. Anomalous temperature acceleration.
5. Device design (LDD) and circuit solutions are effective.

# TDDDB breakdown

1. Historically a NMOS issue, now predominately PMOS failure mode
2. The exact mechanism of time dynamics is still under investigation.
3. Voltage acceleration well described by Anode Hole Injection theory.
4. Soft breakdown allows significant improvement in lifetime. Breakdown becomes correlated for thick oxides.

# Radiation damage

1. A challenging problem that has gotten worse with scaling.
2. The error modes associated with older technologies have been replaced with new issues for modern systems. Understanding the new modes are essential in combating radiation concerns.
3. Circuit solutions like ECC and system redundancy and multi-cycle computing has been particularly effective.



# Measurement

1. Learning to do characterization and failure analysis and understanding the fundamentals of measurement theory essential for reliability physics.
2. Developing characterization techniques and theory behind them is as important as developing reliability theory itself.
3. Differentiate between on-the-fly and stress-measure-stress experiments. Often give very different results.

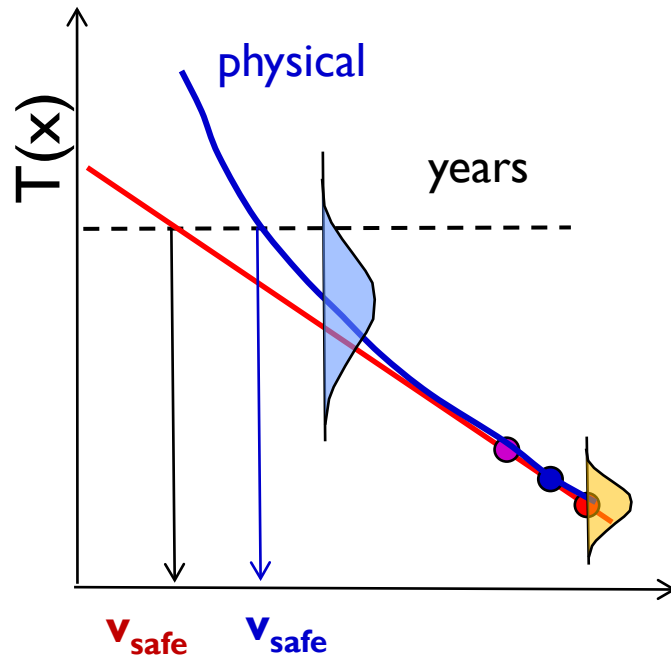
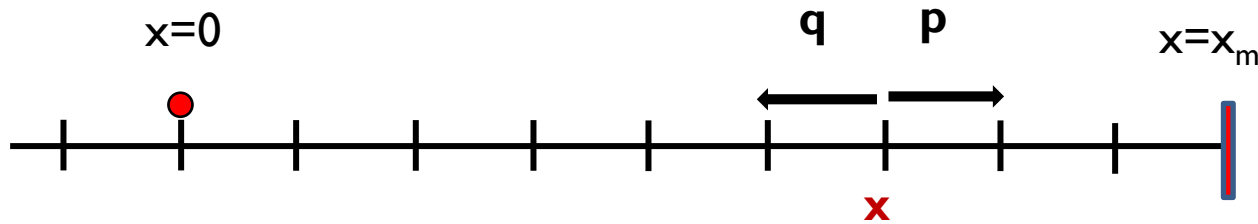
# Data Analysis

1. Distribution is physical, therefore try deriving the distribution from physical principles.
2. Data plotting is key – Median-based analysis, Hazen, Kaplan formula allows unbiased plotting.
3. Fitting the nonlinear data by MLE is most effective. Always get error bounds by bootstrap and use as few parameters as possible (AIC).
4. Important to participate in DOE for most effective analysis. Output can not exceed input.

# Outline

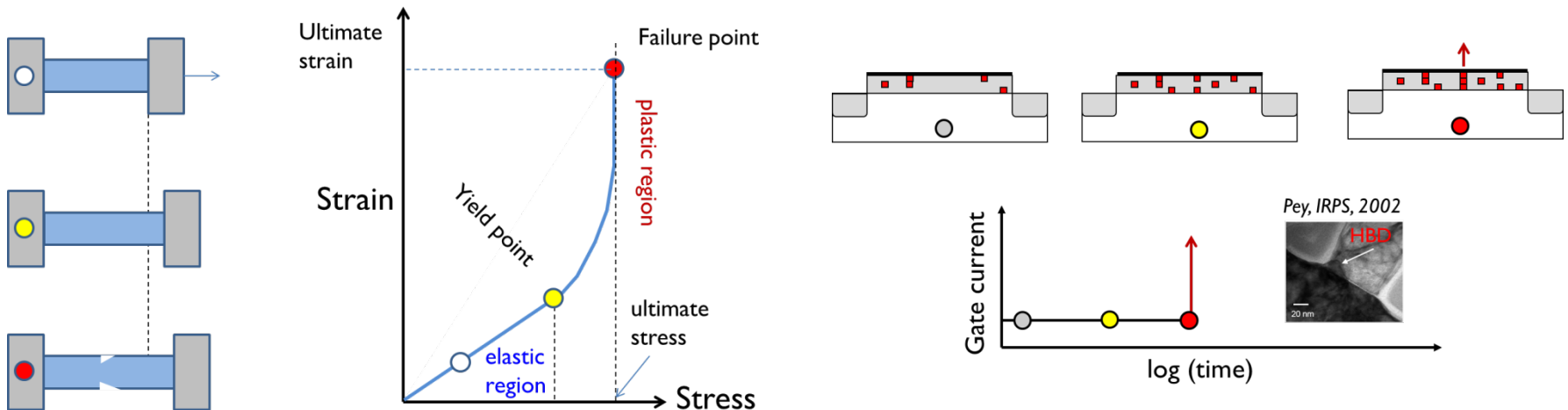
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# Reliability as an extreme non-equilibrium problem with a threshold



# Epilogue: How do we understand so much

Because the world falls apart at  $t = 0^+$ , it behaves completely normally upto that point ( $t = 0^-$ ).



# Epilogue: A contentious field ... because theory matters

Like many field in natural sciences, the theory enables long term projection. If theory is wrong, the whole company will be bankrupt – if the theory is overly conservative, the whole company will also be bankrupt. Therefore, data is vetted carefully over and over again to ensure validity of model projection.

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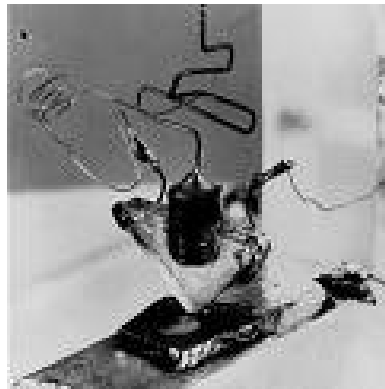
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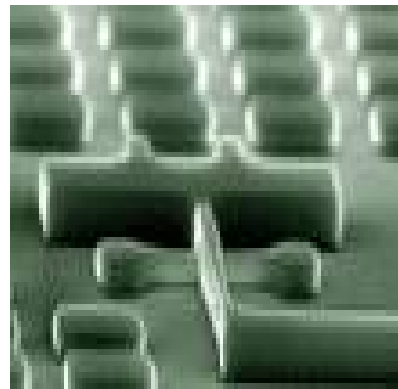
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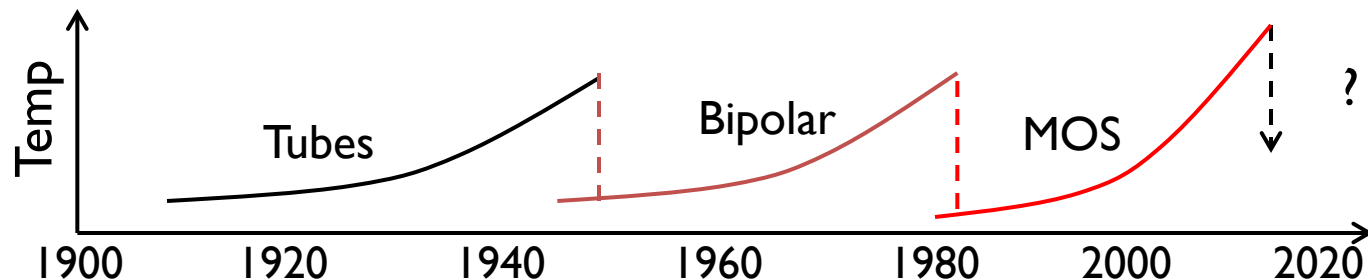
1960-until now

Now ??

Sub-60 mV/dec  
Switches

Bio Sensors

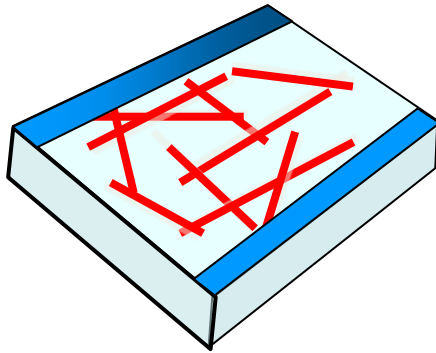
Displays ....



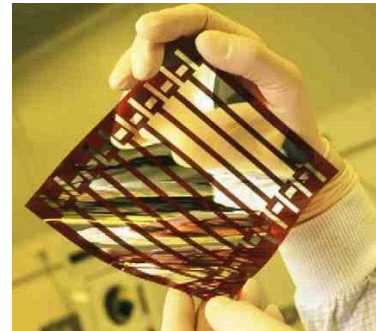
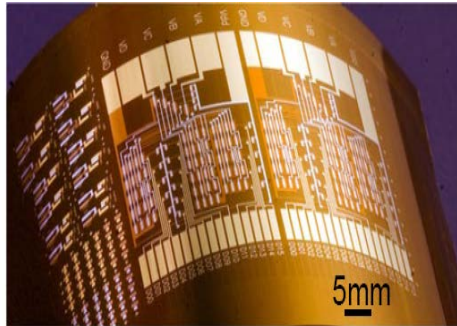
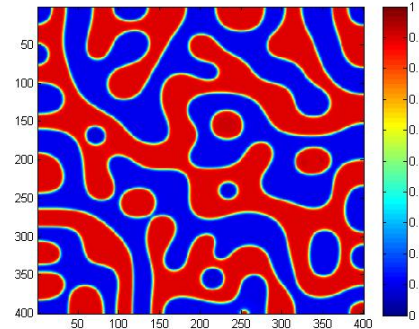


# Evolution in large area electronics

Flexible Electronics



Organic Solar Cells



New materials for novel devices enhance performance, but also accentuate reliability concerns

# Conclusions

We developed a theory of physical reliability to complement the work on Statistical and Empirical reliability already present.

Our hope is to make the topic as scientific and as broadly accepted as 'Fracture Mechanics' .

Hopefully, you have learned something about extreme non-equilibrium statistical mechanics that you will be able to use in wide variety of situations.